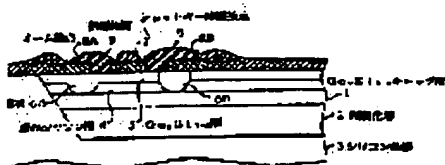

(54) SEMICONDUCTOR DEVICE AND PRODUCING METHOD THEREFOR

**(57)Abstract:**

PURPOSE: To grow a large area hetero body structure of hierarchized GexSi1-x alloy having a low-level threading transfer defect on silicon by growing germanium-silicon alloy at a high temperature and increasing the germanium component with a gradient more than a specified value.

CONSTITUTION: A silicon substrate 3 is prepared. The substrate is a sort of standard (100) direction silicon wafer generally used for producing an integrated circuit. A large area hierarchized layer 2 of germanium-silicon alloy GexSi1-x is grown on the silicon substrate 3 at a high temperature. A growing process is chemical vapor deposition(CVD) or molecular beam epitaxy(MBE). A substrate growth starting temperature is in a range of 850 to 1100°C. Thus, the area of hierarchized alloy exceeds 1200 micrometer 2. The start composition is preferably pure silicon. The germanium forms GexSi1-x with the gradient less than about 25%/micron.

LEGAL STATUS

[Date of request for examination]

02.04.1993

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

2792785

[Date of registration]

19.06.1998

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

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[Date of extinction of right]

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